**Vishay Semiconductors** 

# Hyperfast Rectifier, 2 A FRED Pt<sup>®</sup>



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## LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub>	2 A				
V <sub>R</sub>	1200 V				
V <sub>F</sub> at I <sub>F</sub>	1.6 V				
t <sub>rr</sub>	45 ns				
T <sub>J</sub> max.	175 °C				
Package	SlimSMA HV (DO-221AC)				
Circuit configuration	Single				

### **FEATURES**

soft recovery

- Minimum creepage distance 3.2 mm quaranteed by design
- Comparative Tracking Index: CTI ≥ 600
- Hyperfast recovery time, reduced Qrr, and
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use as clamp, snubber and freewheeling diode in a flyback aux power supplies, bootstrap and desaturate for HV MOSFET and IGBT driver, high frequency rectifiers in a cuk and sepic circuit for LED lighting.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

### **MECHANICAL DATA**

Case: SlimSMA HV (DO-221AC)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V <sub>RRM</sub>		1200	V		
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>Sp</sub> = 95 °C, DC conduction	2	^		
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C, 8.3 ms sine pulse	21	~		
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C		

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HALOGEN

FREE



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<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J$ = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	$V_{BR}, V_{R}$	I <sub>R</sub> = 100 μA	1200	-	-		
		I <sub>F</sub> = 2 A	-	2.0	2.50	v	
Forward voltage drop	V <sub>F</sub>	I <sub>F</sub> = 2 A, T <sub>J</sub> = 125 °C	1.7	1.95	v		
		I <sub>F</sub> = 2 A, T <sub>J</sub> = 150 °C	-	1.6	1.85		
Reverse leakage current	1-	$V_R = V_R$ rated	-	-	3	μA	
neverse leakage current	I <sub>R</sub>	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	30	μA	
lunction consolitance	Ст	V <sub>R</sub> = 1200 V, 1 MHz	-	3.0	-	pF	
Junction capacitance	υŢ	V <sub>R</sub> = 4 V, 1 MHz	-	7.0	-	PΓ	

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	TEST CONDITIONS			MAX.	UNITS	
		$I_{\rm F} = 0.5 \text{ A}, I_{\rm R} = 1 \text{ A}$	A, I <sub>rr</sub> = 0.25 A	-	35	45		
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	105	-	ns A	
		T <sub>J</sub> = 125 °C	I <sub>F</sub> = 2 A, dI <sub>F</sub> /dt = 200 A/μs, V <sub>B</sub> = 800 V	-	145	-		
Deals receiver a current		T <sub>J</sub> = 25 °C		-	4.0	-		
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	5.0	-		
	0	T <sub>J</sub> = 25 °C		-	165	-		
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	315	-	nC	

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C	
Thermal resistance, junction to mount	R <sub>thJM</sub> <sup>(1)</sup>	Device mounted on PCB with 2 x 3.5 mm soldering lands	-	18	22	°C/W	
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Device mounted on PCB with recommended pad size	-	120	-	°C/W	
Approximate weight				0.032		g	
Marking device		Case style SlimSMA HV (DO-221AC)		2>	(12		

#### Note

<sup>(1)</sup> Thermal resistance junction to mount follows JEDEC<sup>®</sup> 51-14 transient dual interface test method (TDIM)

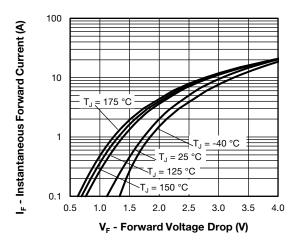


Fig. 1 - Typical Forward Voltage Drop Characteristics

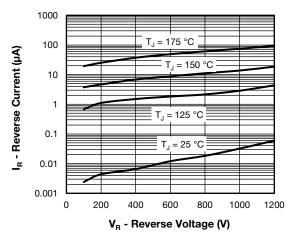


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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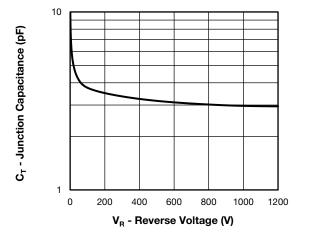


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

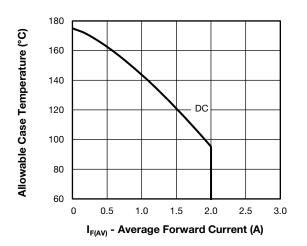


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

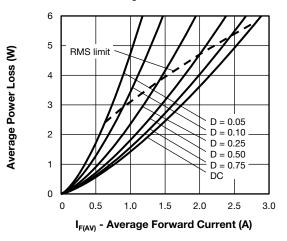


Fig. 5 - Forward Power Loss Characteristics

### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

Pd = forward power loss =  $I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig. 5);  $Pd_{REV}$  = inverse power loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1}$  = rated  $V_R$ 

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VS-E7JX0212-M3

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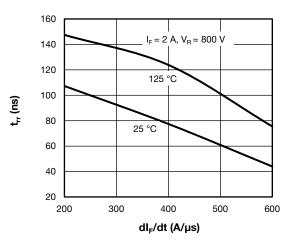


Fig. 6 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

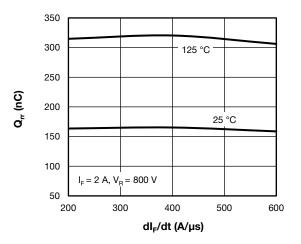


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

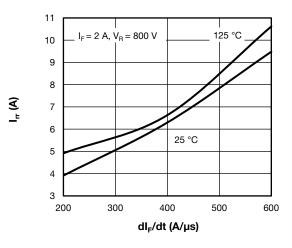


Fig. 8 - I<sub>rr</sub> (A) vs. dI<sub>F</sub>/dt

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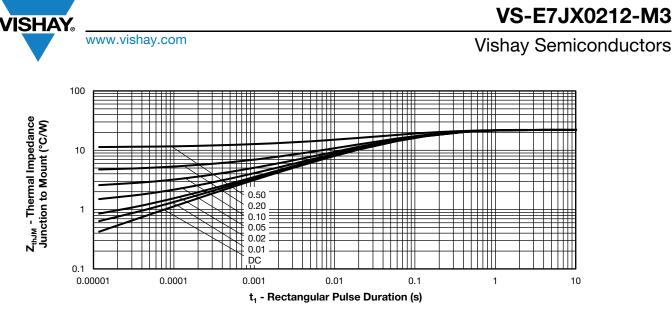


Fig. 9 - Transient Thermal Impedance, Junction to Case

## **ORDERING INFORMATION TABLE**

Device code	vs-	E	7	J	x	02	12	-МЗ
	1	2	3	4	5	6	7	8
	1	- Visl	hay Sen	nicondu	ctors pr	oduct		
	2		cuit conf single d	iguratio diode	ו:			
	3	- 7=	FRED g	generatio	on 7			
	4	- J=	SlimSM	A packa	ige			
	5		cess typ hyperfa	oe, ist recov	very			
	6	- Cur	rent rati	ng (02 =	= 2 A)			
	7	- Vol	tage coo	de (12 =	1200 V	)		
	8	- M3	= halog	en-free,	RoHS-o	compliar	nt, and t	erminati

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER REEL	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-E7JX0212-M3/H	3500	3500	7"diameter plastic tape and reel				
VS-E7JX0212-M3/I	14 000	14 000	13"diameter plastic tape and reel				

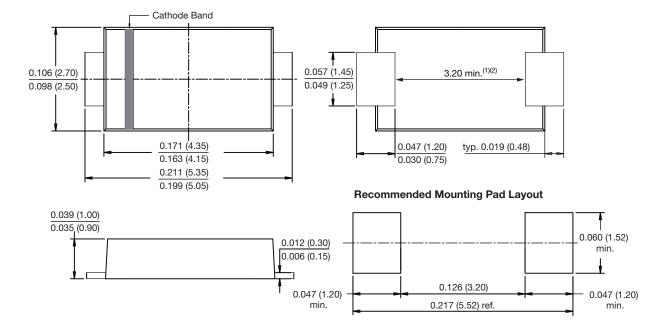
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?97278				
Part marking information	www.vishay.com/doc?95562				
Packaging information	www.vishay.com/doc?88869				

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### **DIMENSIONS** in inches (millimeters)



#### Notes

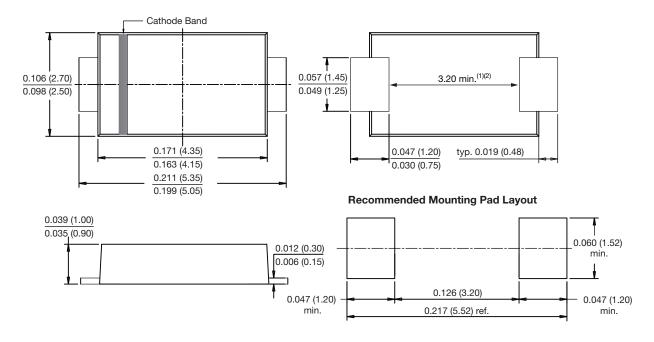
- <sup>(1)</sup> Minimum creepage distance is defined and guaranteed by design
- <sup>(2)</sup> For high voltage applications, end users should consider the relevant guidelines and normative on creepage and clearance distances between device terminals and PCB pads.



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# SlimSMA HV (DO-221AC)

### **DIMENSIONS** in inches (millimeters)



### Notes

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- <sup>(2)</sup> For high voltage applications, end users should consider the relevant guidelines and normative on creepage and clearance distances between device terminals and PCB pads.



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